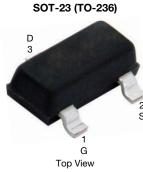
# SQ2318AES

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**Vishay Siliconix** 

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET



#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 Qualified <sup>c</sup>
- 100 % Rg and UIS Tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

D



ROHS COMPLIANT HALOGEN FREE

Marking Code: 8Y

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.031			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.036			
I <sub>D</sub> (A)	8			
Configuration	Single			

Configuration	Single	N-Channel MOSFET		
ORDERING INFORMA	ΓΙΟΝ			
Package		SOT-23		
Lead (Pb)-free and halogen-free	9	SQ2318AES (for detailed order number please see <a href="http://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )		

ABSOLUTE MAXIMUM RATING	(1C = 25 C, unless)	otherwise noted	/	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	40	- V
Gate-source voltage		V <sub>GS</sub>	± 20	
Continuous drain current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	8	
	T <sub>C</sub> = 125 °C		4.6	
Continuous source current (diode conduction)		I <sub>S</sub>	3.8	А
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	32	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	13	
Single pulse avalanche energy	L = 0.1 MH	E <sub>AS</sub>	8	mJ
	T <sub>C</sub> = 25 °C	6	3	W
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	PD	1	VV
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	166	°C/W	
Junction-to-foot (drain)		R <sub>thJF</sub>	50	0/10	

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. When mounted on 1" square PCB (FR4 material)

c. Parametric verification ongoing

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		40	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V <sub>GS</sub> = 10 V	l <sub>D</sub> = 7.9 A	-	0.026	0.031	Ω
Drain actives an etate registeres a	Р	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 7.9 A, T <sub>J</sub> = 125 °C	-	-	0.045	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 7.9 A, T <sub>J</sub> = 175 °C	-	-	0.065	
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 7.3 A	-	0.030	0.036	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 7.9 A		-	30	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	442	553	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V, f = 1 MHz	-	79	99	
Reverse transfer capacitance	C <sub>rss</sub>	1		-	37	46	
Total gate charge <sup>c</sup>	Qg			-	8.7	13	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 3.9 \text{ A}$	-	1.4	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>	1		-	1.6	-	
Gate resistance	Rg	f = 1 MHz		1.5	3.0	4.5	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>				7.5	11	
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 20 \; V, \; R_{\text{L}} = 20 \; \Omega \\ I_{\text{D}} \cong 1 \; A, \; V_{\text{GEN}} = 10 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	8.4	13	- ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	12	18	
Fall time <sup>c</sup>	t <sub>f</sub>			-	5.7	8.5	
Source-Drain Diode Ratings and Char	racteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	32	А
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 5.4 A, V <sub>GS</sub> = 0 V		-	0.8	1.2	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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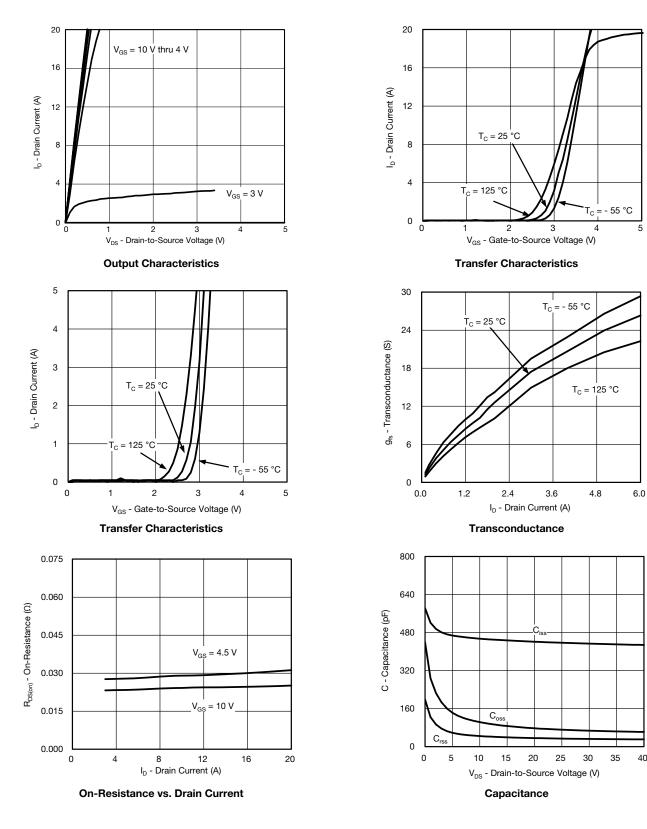


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### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



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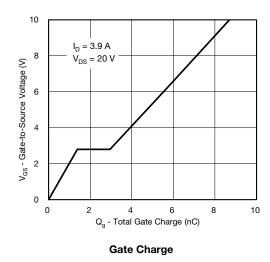
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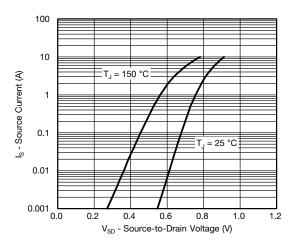
40



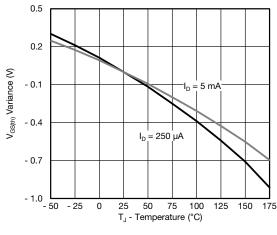
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#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

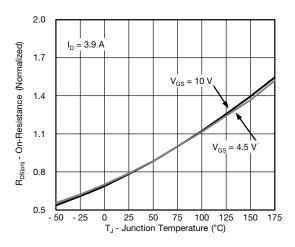




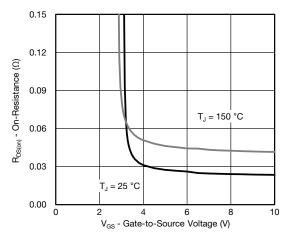
Source Drain Diode Forward Voltage



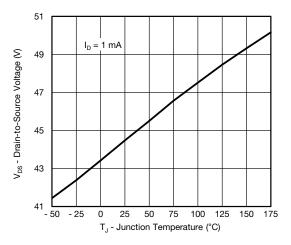
**Threshold Voltage** 



**On-Resistance vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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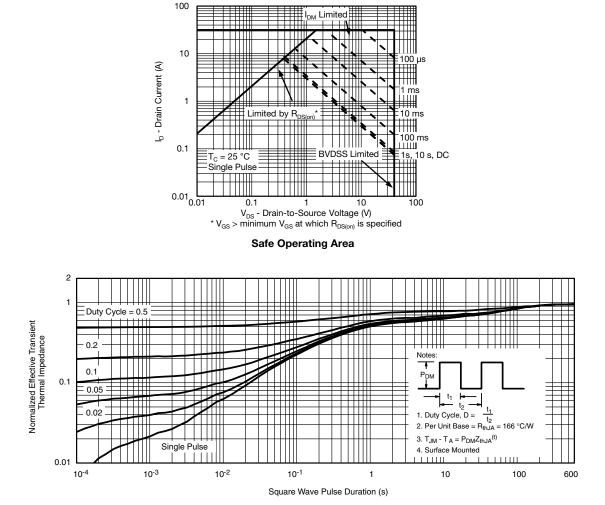
Document Number: 62911

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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



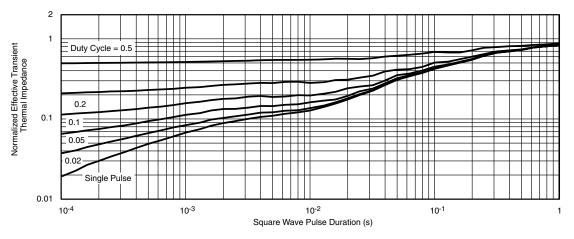
Normalized Thermal Transient Impedance, Junction-to-Ambient



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Document Number: 62911

#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

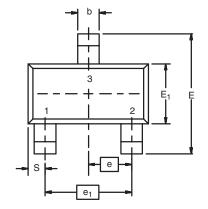
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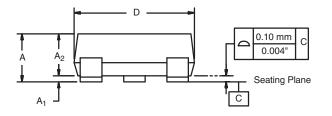


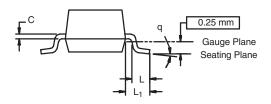
# Package Information

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### SOT-23 (TO-236): 3-LEAD







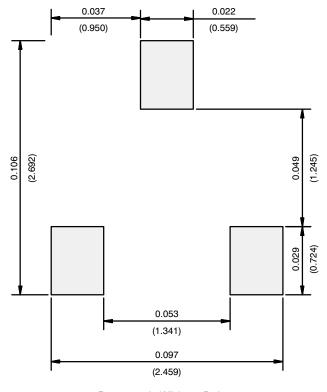
Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01				



# Application Note 826

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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